

DIODE

INTRODUCTION:

The 1N4007/1N4007S series diodes are manufactured to give high current / low forward voltage drop capability.

1N4007 has a lead diameter of $0.7 \pm 0.05\text{mm}$ and 1N4007S has a lead diameter of $0.6 \pm 0.05\text{mm}$.

SPECIFICATIONS

SILICON RECTIFIER DIODES (- 65°C ~ + 175°C)							
Part No	Maximum Average Forward current $I_F(AV)$ in (A)	Maximum Repetitive Reverse Voltage (VRRM) in (V)	Maximum Forward peak Surge current @ 8.3 ms Single half sine wave I_{FSM} in (A)	Maximum Forward Voltage @ $T_A=25^\circ\text{C}$ (VF) in (V)	Maximum Reverse Current @ VRRM IRRM(μA)		Package
					$T_A=25^\circ\text{C}$	$T_A=100^\circ\text{C}$	
1N4007	1.0	1200	30	1.0($I_F=1\text{A}$)	5.0	50	DO-41
1N4007S	1.0	1200	30	1.0($I_F=1\text{A}$)	5.0	50	DO-41

VOLTAGE RANGE: 50 --- 1200 V
CURRENT: 1.0 A

